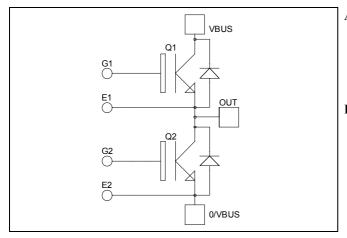
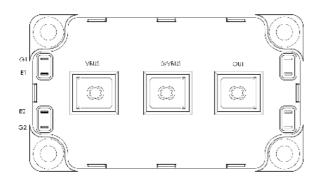


APTGT150A120G

Phase leg Fast Trench + Field Stop IGBT3 Power Module





$V_{CES} = 1200V$ $I_{C} = 150A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	220	
	Continuous Conector Current	$T_C = 80^{\circ}C$	150	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	350	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	690	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	300A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				350	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	J J J J J J J J J J J J J J J J J J J	$T_j = 25^{\circ}C$		1.7	2.1	V
			$T_{j} = 125^{\circ}C$		2.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			10.7		nF
C _{oes}	Output Capacitance		$V_{CE} = 25V$		0.56		
C _{res}	Reverse Transfer Capacitance	f = 1 MHz			0.48		
T _{d(on)}	Turn-on Delay Time	Inductive Switch	ning (25°C)		280		
T _r	Rise Time		$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $U = 150A$		40		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$			420		
$T_{\rm f}$	Fall Time	$R_{\rm G} = 2.2\Omega$			75		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 150A$ $R_G = 2.2\Omega$			290		ns
Tr	Rise Time				45		
T _{d(off)}	Turn-off Delay Time				520		
$T_{\rm f}$	Fall Time				90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$	$T_j = 125^{\circ}C$		14		mJ
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$I_{C} = 150A$ $R_{G} = 2.2\Omega$	$T_j = 125^{\circ}C$		16		1113

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$			250	μA
Rivi			$T_{j} = 125^{\circ}C$			600	·
$I_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		150		Α
V _F	Diode Forward Voltage	$I_F = 150A$	$T_i = 25^{\circ}C$		1.6	2.1	V
• F	blode i of ward voltage		$T_i = 125^{\circ}C$		1.6		, v
t _{rr}	Reverse Recovery Time	$I_F = 150A$ $V_R = 600V$ $di/dt = 2500A/\mu s$	$T_j = 25^{\circ}C$		170		ns
۹r			$T_{j} = 125^{\circ}C$		280		no
0	Reverse Recovery Charge		$T_j = 25^{\circ}C$		14		μC
Q _{rr}			$T_{j} = 125^{\circ}C$		28		μĊ
Er	Reverse Recovery Energy		$T_i = 25^{\circ}C$		6		mJ
Ľr	Reverse Recovery Energy		$T_{j} = 125^{\circ}C$		11		1113

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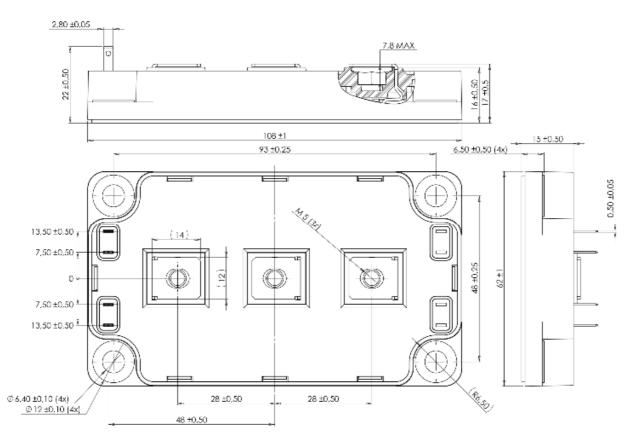
2 - 6



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance IGBT Diode				0.18	°C/W	
R _{th} JC					0.32		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Torque		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

SP6 Package outline (dimensions in mm)



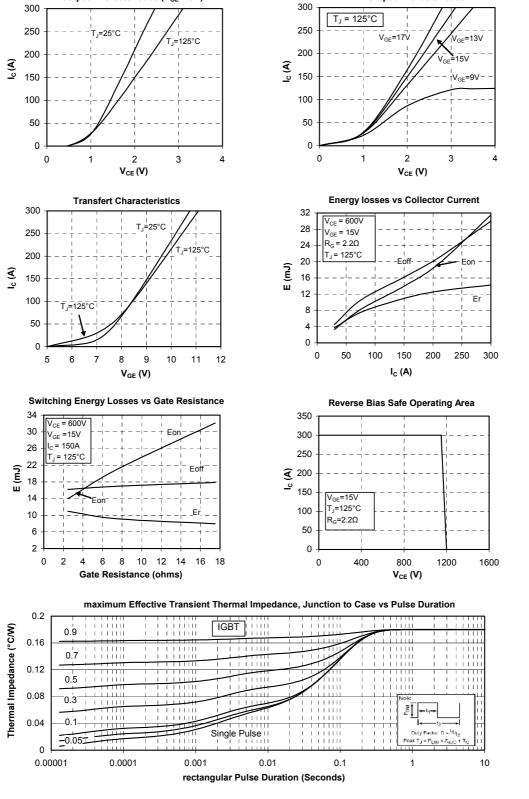
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com



Output Characteristics (V_{GE}=15V)

Typical Performance Curve

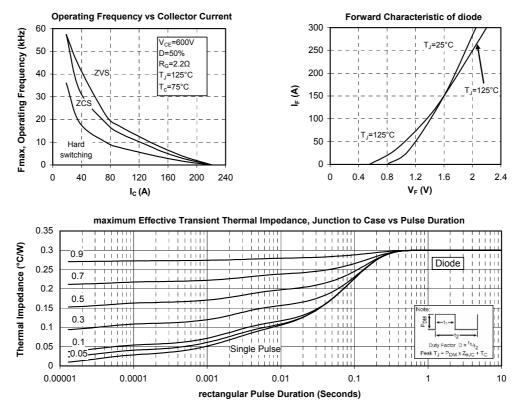
APTGT150A120G



APTGT150A120G-Rev 2 October, 2012



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5 - 6



APTGT150A120G

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